

PNP high-voltage transistor

BSS63

FEATURES

- Low current (max. 100 mA)
- High voltage (max. 100 V).

APPLICATIONS

- High-voltage general purpose
- Switching applications.

DESCRIPTION

PNP high-voltage transistor in a SOT23 plastic package.
NPN complement: BSS64.

MARKING

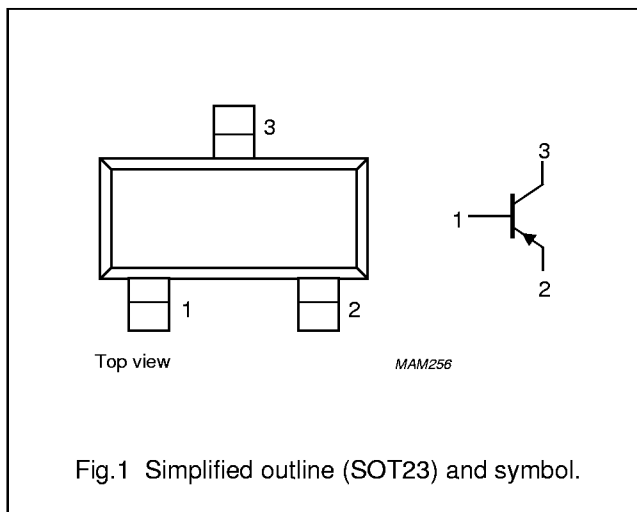
TYPE NUMBER	MARKING CODE ⁽¹⁾
BSS63	BM*

Note

1. * = p : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–110	V
V_{CEO}	collector-emitter voltage	open base	–	–100	V
V_{EBO}	emitter-base voltage	open collector	–	–6	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–100	mA
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -90\text{ V}$	–	–	–100	nA
		$I_E = 0; V_{CB} = -90\text{ V}; T_j = 150\text{ °C}$	–	–	–50	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -6\text{ V}$	–	–	–100	nA
h_{FE}	DC current gain	$I_C = -10\text{ mA}; V_{CE} = -1\text{ V}$	30	–	–	
		$I_C = -25\text{ mA}; V_{CE} = -1\text{ V}$	30	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -25\text{ mA}; I_B = -2.5\text{ mA}$	–	–	–250	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -25\text{ mA}; I_B = -2.5\text{ mA}$	–	–	–900	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	3	–	pF
f_T	transition frequency	$I_C = -25\text{ mA}; V_{CE} = -5\text{ V}; f = 100\text{ MHz}$	50	85	–	MHz

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23

